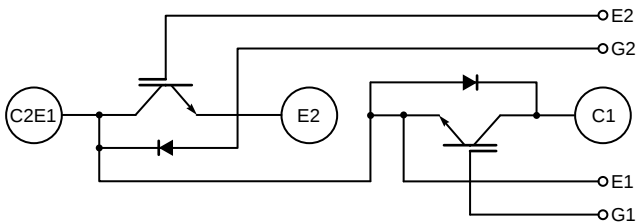
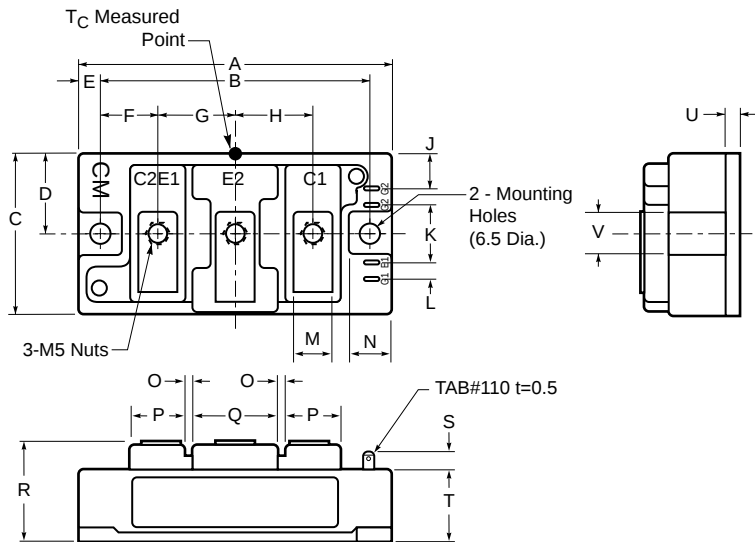


**MITSUBISHI IGBT MODULES**  
**CM75DU-12H**  
HIGH POWER SWITCHING USE  
INSULATED TYPE



**Outline Drawing and Circuit Diagram**

| Dimensions | Inches    | Millimeters |
|------------|-----------|-------------|
| A          | 3.7       | 94.0        |
| B          | 3.15±0.01 | 80.0±0.25   |
| C          | 1.89      | 48.0        |
| D          | 0.94      | 24.0        |
| E          | 0.28      | 7.0         |
| F          | 0.67      | 17.0        |
| G          | 0.91      | 23.0        |
| H          | 0.91      | 23.0        |
| J          | 0.43      | 11.0        |
| K          | 0.71      | 18.0        |
| L          | 0.16      | 4.0         |

| Dimensions | Inches           | Millimeters    |
|------------|------------------|----------------|
| M          | 0.47             | 12.0           |
| N          | 0.53             | 13.5           |
| O          | 0.1              | 2.5            |
| P          | 0.63             | 16.0           |
| Q          | 0.98             | 25.0           |
| R          | 1.18 +0.04/-0.02 | 30.0 +1.0/-0.5 |
| S          | 0.3              | 7.5            |
| T          | 0.83             | 21.2           |
| U          | 0.16             | 4.0            |
| V          | 0.51             | 13.0           |



**Description:**

Mitsubishi IGBT Modules are designed for use in switching applications. Each module consists of two IGBTs in a half-bridge configuration with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

**Features:**

- ☐ Low Drive Power
- ☐ Low  $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery Free-Wheel Diode
- ☐ High Frequency Operation
- ☐ Isolated Baseplate for Easy Heat Sinking

**Applications:**

- ☐ AC Motor Control
- ☐ Motion/Servo Control
- ☐ UPS
- ☐ Welding Power Supplies

**Ordering Information:**

Example: Select the complete module number you desire from the table - i.e. CM75DU-12H is a 600V ( $V_{CES}$ ), 75 Ampere Dual IGBT Module.

| Type | Current Rating<br>Amperes | $V_{CES}$<br>Volts (x 50) |
|------|---------------------------|---------------------------|
| CM   | 75                        | 12                        |

## CM75DU-12H

HIGH POWER SWITCHING USE  
INSULATED TYPEAbsolute Maximum Ratings,  $T_j = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

| Ratings                                                                                       | Symbol           | CM75DU-12H | Units                     |
|-----------------------------------------------------------------------------------------------|------------------|------------|---------------------------|
| Junction Temperature                                                                          | $T_j$            | -40 to 150 | $^{\circ}\text{C}$        |
| Storage Temperature                                                                           | $T_{\text{stg}}$ | -40 to 125 | $^{\circ}\text{C}$        |
| Collector-Emitter Voltage (G-E SHORT)                                                         | $V_{\text{CES}}$ | 600        | Volts                     |
| Gate-Emitter Voltage (C-E SHORT)                                                              | $V_{\text{GES}}$ | $\pm 20$   | Volts                     |
| Collector Current ( $T_c = 25^{\circ}\text{C}$ )                                              | $I_c$            | 75         | Amperes                   |
| Peak Collector Current                                                                        | $I_{\text{CM}}$  | 150*       | Amperes                   |
| Emitter Current** ( $T_c = 25^{\circ}\text{C}$ )                                              | $I_E$            | 75         | Amperes                   |
| Peak Emitter Current**                                                                        | $I_{\text{EM}}$  | 150*       | Amperes                   |
| Maximum Collector Dissipation ( $T_c = 25^{\circ}\text{C}$ , $T_j \leq 150^{\circ}\text{C}$ ) | $P_c$            | 310        | Watts                     |
| Mounting Torque, M5 Main Terminal                                                             | —                | 2.5~3.5    | $\text{N} \cdot \text{m}$ |
| Mounting Torque, M6 Mounting                                                                  | —                | 3.5~4.5    | $\text{N} \cdot \text{m}$ |
| Weight                                                                                        | —                | 310        | Grams                     |
| Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)                                     | $V_{\text{ISO}}$ | 2500       | $V_{\text{rms}}$          |

\* Pulse width and repetition rate should be such that the device junction temperature ( $T_j$ ) does not exceed  $T_{j(\text{max})}$  rating.

\*\*Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

Static Electrical Characteristics,  $T_j = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

| Characteristics                      | Symbol               | Test Conditions                                                                   | Min. | Typ. | Max. | Units         |
|--------------------------------------|----------------------|-----------------------------------------------------------------------------------|------|------|------|---------------|
| Collector-Cutoff Current             | $I_{\text{CES}}$     | $V_{\text{CE}} = V_{\text{CES}}$ , $V_{\text{GE}} = 0\text{V}$                    | —    | —    | 1    | mA            |
| Gate Leakage Voltage                 | $I_{\text{GES}}$     | $V_{\text{GE}} = V_{\text{GES}}$ , $V_{\text{CE}} = 0\text{V}$                    | —    | —    | 0.5  | $\mu\text{A}$ |
| Gate-Emitter Threshold Voltage       | $V_{\text{GE(th)}}$  | $I_c = 7.5\text{mA}$ , $V_{\text{CE}} = 10\text{V}$                               | 4.5  | 6    | 7.5  | Volts         |
| Collector-Emitter Saturation Voltage | $V_{\text{CE(sat)}}$ | $I_c = 75\text{A}$ , $V_{\text{GE}} = 15\text{V}$ , $T_j = 25^{\circ}\text{C}$    | —    | 2.4  | 3.0  | Volts         |
|                                      |                      | $I_c = 75\text{A}$ , $V_{\text{GE}} = 15\text{V}$ , $T_j = 125^{\circ}\text{C}$   | —    | 2.6  | —    | Volts         |
| Total Gate Charge                    | $Q_G$                | $V_{\text{CC}} = 300\text{V}$ , $I_c = 75\text{A}$ , $V_{\text{GE}} = 15\text{V}$ | —    | 150  | —    | nC            |
| Emitter-Collector Voltage**          | $V_{\text{EC}}$      | $I_E = 75\text{A}$ , $V_{\text{GE}} = 0\text{V}$                                  | —    | —    | 2.6  | Volts         |

\*\*Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

Dynamic Electrical Characteristics,  $T_j = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

| Characteristics                 |                     | Symbol       | Test Conditions                    | Min. | Typ. | Max. | Units   |
|---------------------------------|---------------------|--------------|------------------------------------|------|------|------|---------|
| Input Capacitance               |                     | $C_{ies}$    | $V_{CE} = 10V, V_{GE} = 0V$        | —    | —    | 6.6  | nF      |
| Output Capacitance              |                     | $C_{oes}$    |                                    | —    | —    | 3.6  | nF      |
| Reverse Transfer Capacitance    |                     | $C_{res}$    |                                    | —    | —    | 1    | nF      |
| Resistive                       | Turn-on Delay Time  | $t_{d(on)}$  | $V_{CC} = 300V, I_C = 75A,$        | —    | —    | 100  | ns      |
| Load                            | Rise Time           | $t_r$        | $V_{GE1} = V_{GE2} = 15V,$         | —    | —    | 250  | ns      |
| Switch                          | Turn-off Delay Time | $t_{d(off)}$ | $R_G = 8.3\Omega,$ Resistive       | —    | —    | 200  | ns      |
| Times                           | Fall Time           | $t_f$        | Load Switching Operation           | —    | —    | 300  | ns      |
| Diode Reverse Recovery Time**   |                     | $t_{rr}$     | $I_E = 75A, di_E/dt = -150A/\mu s$ | —    | —    | 160  | ns      |
| Diode Reverse Recovery Charge** |                     | $Q_{rr}$     | $I_E = 75A, di_E/dt = -150A/\mu s$ | —    | 0.18 | —    | $\mu C$ |

\*\*Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

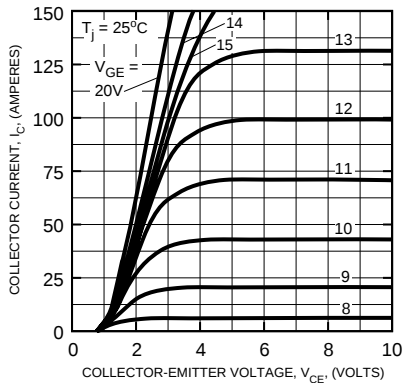
Thermal and Mechanical Characteristics,  $T_j = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

| Characteristics                      | Symbol                | Test Conditions                    | Min. | Typ.  | Max. | Units                       |
|--------------------------------------|-----------------------|------------------------------------|------|-------|------|-----------------------------|
| Thermal Resistance, Junction to Case | $R_{\text{th(j-c)Q}}$ | Per IGBT 1/2 Module                | —    | —     | 0.4  | $^{\circ}\text{C}/\text{W}$ |
| Thermal Resistance, Junction to Case | $R_{\text{th(j-c)D}}$ | Per FWDi 1/2 Module                | —    | —     | 0.9  | $^{\circ}\text{C}/\text{W}$ |
| Contact Thermal Resistance           | $R_{\text{th(c-f)}}$  | Per Module, Thermal Grease Applied | —    | 0.035 | —    | $^{\circ}\text{C}/\text{W}$ |

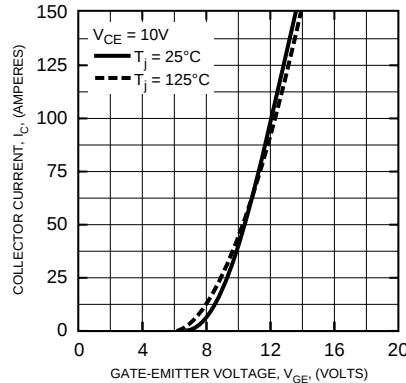
# CM75DU-12H

HIGH POWER SWITCHING USE  
INSULATED TYPE

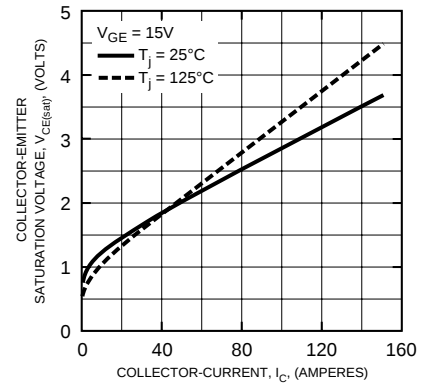
OUTPUT CHARACTERISTICS  
(TYPICAL)



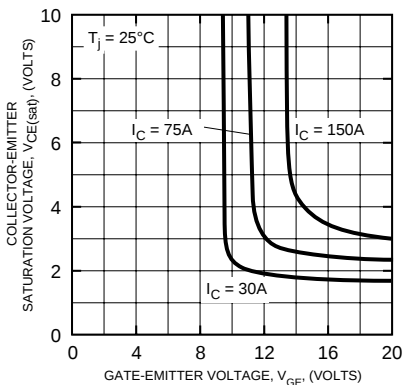
TRANSFER CHARACTERISTICS  
(TYPICAL)



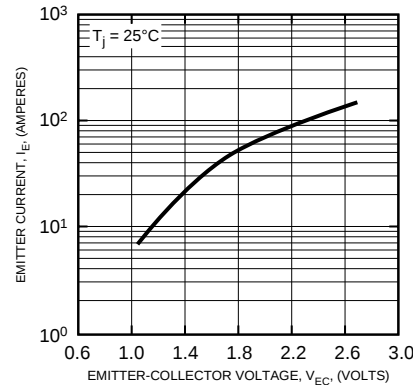
COLLECTOR-EMITTER  
SATURATION VOLTAGE CHARACTERISTICS  
(TYPICAL)



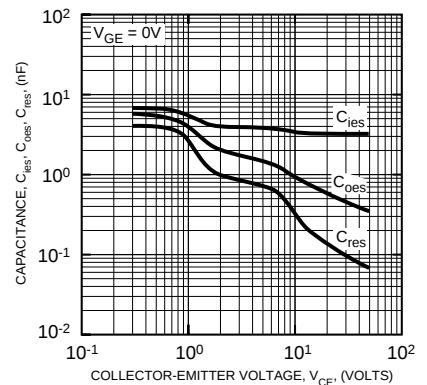
COLLECTOR-EMITTER  
SATURATION VOLTAGE CHARACTERISTICS  
(TYPICAL)



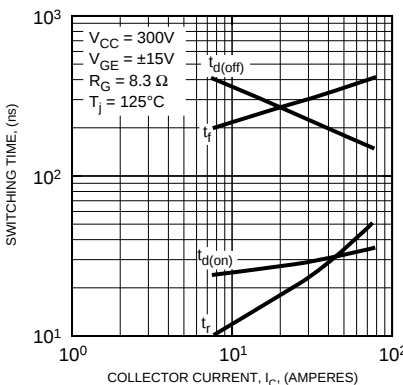
FREE-WHEEL DIODE  
FORWARD CHARACTERISTICS  
(TYPICAL)



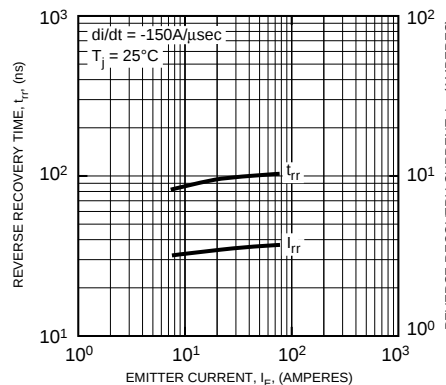
CAPACITANCE VS.  $V_{CE}$   
(TYPICAL)



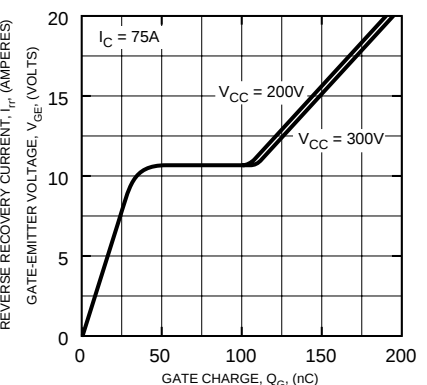
HALF-BRIDGE  
SWITCHING CHARACTERISTICS  
(TYPICAL)



REVERSE RECOVERY CHARACTERISTICS  
(TYPICAL)



GATE CHARGE,  $V_{GE}$



# CM75DU-12H

HIGH POWER SWITCHING USE  
INSULATED TYPE

